EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1996	(substrate wafer) with (isolation adj trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:40
L2	240444	((isolation insulat$4 dielectric) adj (region film layer)) with (substrate wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:42
L3	1231	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:42
L4	326	3 and (memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:42
L5	210	4 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:43
L6	135	@ad <="20030527" and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:44
L7	79	6 and ((isolation adj trench) with (etch$4 remov$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:45
L8	44	7 and (anneal$4 heat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:46

L9	7	("5612914" | "5674764" | "5859888" | "5976933" | "6049482" | "6235583" | "6342715").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/02 17:09
L10	2	("6818508").URPN.	USPAT	OR	OFF	2006/03/02 17:11
S2	760	(isolat$4 adj trench) near3 etch$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:54
S3	1	(anneal$4 near4 (floating adj gate)) same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:34
S4	1	(anneal$4 with (floating adj gate)) same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:35
S5	77	anneal$4 same (water adj vapor adj atmosphere)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:50
S6	2	S2 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:49
S9	39	S5 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:53
S10	2	S9 and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:50

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S11	708	S2 and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:54
S12	204	S11 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:55
S13	152	S12 and (insulat$4 adj (film or layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:56
S14	114	@ad <="20030527" and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 23:18
S15	95	(non-volatile adj memory adj cell) and (tunnel adj insulat$4 adj (film or layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 22:25
S16	93	S15 and ((floating adj gate) or (gate adj electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 21:59
S17	88	S16 and (control adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 22:00
S18	74	@ad <="20030527" and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 16:44
S19	680	438/197.ccls.	USPAT	OR	OFF	2005/09/24 23:18

S20	5	S19 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:36
S21	1313	438/257.ccls.	USPAT	OR	OFF	2005/09/24 23:20
S22	131	S21 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:55
S23	113	@ad <="20030527" and S22	USPAT	OR	OFF	2006/03/02 16:39
S24	415	438/259.ccls.	USPAT	OR	OFF	2005/09/24 23:22
S25	30	S24 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 22:58
S26	25	@ad <="20030527" and S25	USPAT	OR	OFF	2005/09/24 22:58
S27	636	438/264.ccls.	USPAT	OR	OFF	2005/09/24 22:58
S28	47	S27 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 23:16
S29	46	@ad <="20030527" and S28	USPAT	OR	OFF	2005/09/24 23:16
S30	266	438/294.ccls.	USPAT	OR	OFF	2005/09/24 23:16
S31	4	S30 and (non-volatile adj memory adj cell)	USPAT	OR	OFF	2005/09/24 23:19
S32	4	@ad <="20030527" and S31	USPAT	OR	OFF	2005/09/24 23:20
S33	635	438/197.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:18
S35	5	S33 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:20
S36	668	438/257.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:20
S37	67	S36 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:22
S38	40	@ad <="20030527" and S37	US-PGPUB	OR	OFF	2005/09/24 23:22
S39	127	438/259.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:22
S40	9	S39 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:28
S41	5	@ad <="20030527" and S40	US-PGPUB	OR	OFF	2005/09/24 23:22
S42	131	438/264.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:23
S43	8	S42 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:30
S44	72	438/294.ccls.	US-PGPUB	OR	OFF	2005/09/24 23:30
S45	1	S44 and (non-volatile adj memory adj cell)	US-PGPUB	OR	OFF	2005/09/24 23:30